

TDS:EMIC

拓電半導體

自主封測 品質把控 售後保障

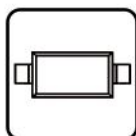
WEB | WWW.TDSEMIC.COM



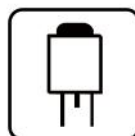
電源管理



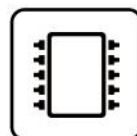
顯示驅動



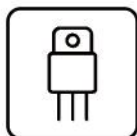
二三極管



LDO穩壓器



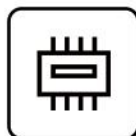
觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

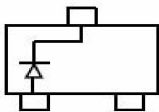
BAT54A KL2-TD

產品規格說明書

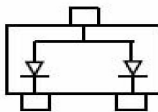
BAT54/A/C/S SCHOTTKY DIODES

FEATURES

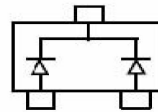
- ◆ Extremely Fast Switching Speed



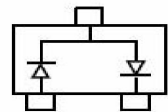
BAT54 MARKING:KL1



BAT54A MARKING:KL2



BAT54C MARKING:KL3



BAT54S MARKING:KL4

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	30	V
Forward Continuous Current	I _{FM}	200	mA
Power Dissipation	P _D	200	mW
Storage temperature	T _{STG}	-55-150	°C

Electrical Characteristics @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _{(BR)R}	30			V	I _R =100μA
Forward voltage	V _{F1}			0.24	V	I _F =0.1mA
	V _{F2}			0.32	V	I _F =1mA
	V _{F3}			0.40	V	I _F =10mA
	V _{F4}			0.50	V	I _F =30mA
	V _{F5}			1	V	I _F =100mA
Reverse current	I _R			2	μA	V _R =25V
Diode Capacitance	C _D			10	pF	V _R =1V, f=1MHz
Reverse Recovery Time	t _{rr}			5	nS	I _F =I _R =10mA I _{rr} =0.1X I _R , R _L =100Ω

Typical Characteristics

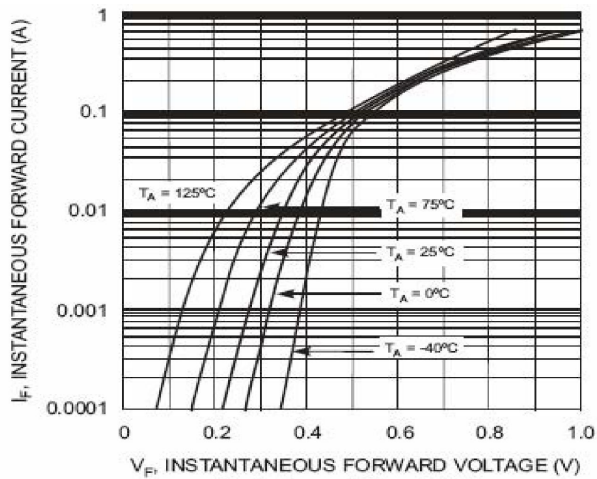


Fig. 1 Forward Characteristics

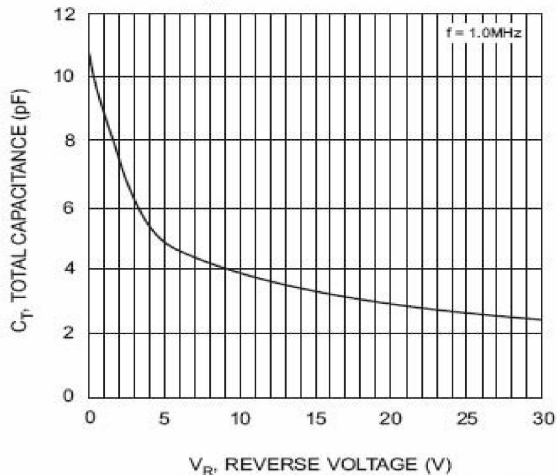


Fig. 3 Typical Capacitance vs. Reverse Voltage

BAT54/A/C/S

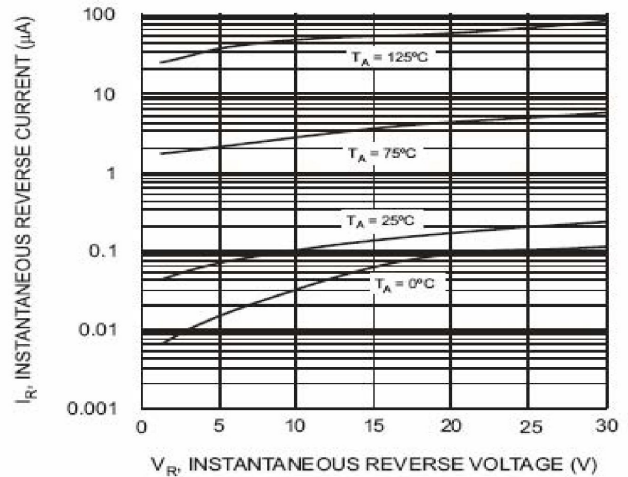


Fig. 2 Typical Reverse Characteristics

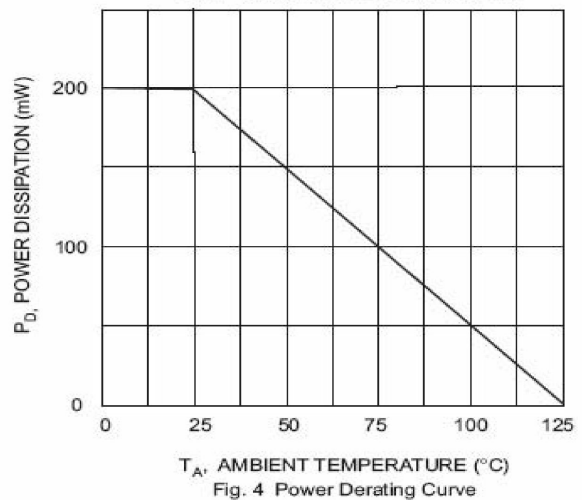


Fig. 4 Power Derating Curve